

# CMOS, $\pm 5$ V/+5 V, 4 $\Omega$ , Single SPDT Switch

ADG619-EP

#### **FEATURES**

14  $\Omega$  (maximum) on resistance 1.4 Ω (maximum) on-resistance flatness 2.7 V to 5.5 V single supply ±2.7 V to ±5.5 V dual supply **Rail-to-rail operation** 8-lead SOT-23 Typical power consumption (<0.1 µW) TTL-/CMOS-compatible inputs Supports defense and aerospace applications (AQEC standard) Military temperature range: -55°C to +125°C Controlled manufacturing baseline One assembly and test site One fabrication site **Enhanced product change notification** Qualification data available on request

#### **APPLICATIONS**

Automatic test equipment
Power routing
Communication systems
Data acquisition systems
Sample-and-hold systems
Avionics
Relay replacement
Battery-powered systems

#### **GENERAL DESCRIPTION**

The ADG619-EP is a monolithic, CMOS single-pole double-throw (SPDT) switch.

The ADG619-EP offers a low on resistance of 4  $\Omega$ , which is matched to within 0.7  $\Omega$  between channels. These switches also provide low power dissipation, yet result in high switching speeds. The ADG619-EP exhibits break-before-make switching action, thus preventing momentary shorting when switching channels.

The ADG619-EP is available in an 8-lead SOT-23 package.

Additional application and technical information can be found in the ADG619 data sheet.

#### **FUNCTIONAL BLOCK DIAGRAM**

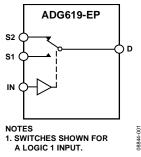


Figure 1.

### **PRODUCT HIGHLIGHTS**

- 1. Low on resistance  $(R_{ON})$ : 4  $\Omega$  typical.
- 2. Dual  $\pm 2.7$  V to  $\pm 5.5$  V or single 2.7 V to 5.5 V supplies.
- 3. Low power dissipation.
- 4. Fast  $t_{ON}/t_{OFF}$ .
- 5. Tiny, 8-lead SOT-23 package.

# **TABLE OF CONTENTS**

Features	Single Supply	4
Applications 1	Absolute Maximum Ratings	5
Functional Block Diagram1	ESD Caution	5
General Description1	Pin Configurations and Function Descriptions	<i>6</i>
Product Highlights 1	Typical Performance Characteristics	7
Revision History		8
Specifications	Outline Dimensions	. 10
Dual Supply3		. 10

## **REVISION HISTORY**

11/10—Revision 0: Initial Version

# **SPECIFICATIONS**

## **DUAL SUPPLY**

 $V_{DD}$  = +5 V ± 10%,  $V_{SS}$  = -5 V ± 10%, GND = 0 V. All specifications -55°C to +125°C, unless otherwise noted.

Table 1.

Parameter	+25°C	−55°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		$V_{SS}$ to $V_{DD}$	V	$V_{DD} = +4.5 \text{ V}, V_{SS} = -4.5 \text{ V}$
On Resistance (R <sub>ON</sub> )	4		Ωtyp	$V_{s} = \pm 4.5 \text{ V}, I_{DS} = -10 \text{ mA}; \text{ see Figure 9}$
	6.5	10	Ωmax	
$R_{ON}$ Match Between Channels ( $\Delta R_{ON}$ )	0.7		Ωtyp	$V_S = \pm 4.5 \text{ V}, I_{DS} = -10 \text{ mA}$
	1.1	1.45	Ωmax	
On-Resistance Flatness (R <sub>FLAT (ON)</sub> )	0.7		Ωtyp	$V_S = \pm 3.3 \text{ V, } I_{DS} = -10 \text{ mA}$
	1.35	1.6	Ω max	
LEAKAGE CURRENTS				$V_{DD} = +5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
Source Off Leakage, I <sub>s</sub> (Off)	±0.01		nA typ	$V_{s} = \pm 4.5 \text{ V}, V_{D} = \mp 4.5 \text{ V}; \text{ see Figure 10}$
	±0.25	±3	nA max	
Channel On Leakage, I <sub>D</sub> , I <sub>S</sub> (On)	±0.01		nA typ	$V_{s} = V_{D} = \pm 4.5 \text{ V}$ ; see Figure 11
J-, U 3 (- ,	±0.25	±25	nA max	, 3,
DIGITAL INPUTS				
Input High Voltage, V <sub>INH</sub>		2.4	V min	
Input Low Voltage, V <sub>INI</sub>		0.8	V max	
Input Current, I <sub>INI</sub> or I <sub>INH</sub>	0.005		μA typ	$V_{IN} = V_{INI}$ or $V_{INH}$
		±0.1	μA max	14 142 141
Digital Input Capacitance, C <sub>IN</sub>	2		pF typ	
DYNAMIC CHARACTERISTICS <sup>1</sup>				
t <sub>on</sub>	80		ns typ	$R_1 = 300 \Omega, C_1 = 35 pF$
	120	215	ns max	V <sub>s</sub> = 3.3 V; see Figure 12
t <sub>OFF</sub>	45		ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	75	105	ns max	V <sub>s</sub> = 3.3 V; see Figure 12
Break-Before-Make Time Delay, t <sub>BBM</sub>	40		ns typ	$R_L = 300 \Omega, C_L = 35 pF$
		10	ns min	$V_{S1} = V_{S2} = 3.3 \text{ V}$ ; see Figure 13
Charge Injection	110		pC typ	$V_S = 0 \text{ V}$ , $R_S = 0 \Omega$ , $C_L = 1 \text{ nF}$ ; see Figure 14
Off Isolation	-67		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 15
Channel-to-Channel Crosstalk	-67		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 16
Bandwidth –3 dB	190		MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ ; see Figure 17
C <sub>s</sub> (Off)	25		pF typ	f = 1 MHz
$C_D, C_S$ (On)	95		pF typ	f = 1 MHz
POWER REQUIREMENTS				$V_{DD} = +5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
I <sub>DD</sub>	0.001		μA typ	Digital inputs = 0 V or 5.5 V
		1.0	μA max	
I <sub>ss</sub>	0.001		μA typ	Digital inputs = 0 V or 5.5 V
		1.0	μA max	

<sup>&</sup>lt;sup>1</sup> Guaranteed by design, not subject to production test.

## **SINGLE SUPPLY**

 $V_{DD}$  = 5 V ± 10%,  $V_{SS}$  = 0 V, GND = 0 V. All specifications –55°C to +125°C, unless otherwise noted.

Table 2.

Parameter	+25°C	-55°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		0 V to V <sub>DD</sub>	٧	$V_{DD} = 4.5 \text{ V}, V_{SS} = 0 \text{ V}$
On Resistance (R <sub>ON</sub> )	7		Ωtyp	$V_s = 0 \text{ V to } 4.5 \text{ V, } I_{DS} = -10 \text{ mA; see Figure 9}$
	10	14	Ω max	
$R_{ON}$ Match Between Channels ( $\Delta R_{ON}$ )	0.8		Ωtyp	$V_S = 0 \text{ V to } 4.5 \text{ V, } I_{DS} = -10 \text{mA}$
	1.1	1.4	Ω max	
On-Resistance Flatness (R <sub>FLAT (ON)</sub> )	0.5		Ωtyp	$V_S = 1.5 \text{ V to } 3.3 \text{ V, } I_{DS} = -10 \text{ mA}$
		1.4	Ωmax	
LEAKAGE CURRENTS				$V_{DD} = 5.5 \text{ V}$
Source Off Leakage, I <sub>s</sub> (Off)	±0.01		nA typ	$V_S = 1 \text{ V}/4.5 \text{ V}, V_D = 4.5 \text{ V}/1 \text{ V}; \text{ see Figure 10}$
	±0.25	±3	nA max	
Channel On Leakage, $I_D$ , $I_S$ (On)	±0.01		nA typ	$V_{S} = V_{D} = 1 \text{ V}/4.5 \text{ V}$ ; see Figure 11
	±0.25	±25	nA max	
DIGITAL INPUTS				
Input High Voltage, V <sub>INH</sub>		2.4	V min	
Input Low Voltage, V <sub>INL</sub>		0.8	V max	
Input Current, I <sub>INL</sub> or I <sub>INH</sub>	0.005		μA typ	$V_{IN} = V_{INL}$ or $V_{INH}$
		±0.1	μA max	
Digital Input Capacitance, C <sub>IN</sub>	2		pF typ	
DYNAMIC CHARACTERISTICS <sup>1</sup>				
t <sub>on</sub>	120		ns typ	$R_{L} = 300 \Omega, C_{L} = 35 pF$
	220	390	ns max	$V_s = 3.3 \text{ V}$ ; see Figure 12
t <sub>off</sub>	50		ns typ	$R_{L} = 300 \Omega, C_{L} = 35 pF$
	75	135	ns max	$V_s = 3.3 \text{ V}$ ; see Figure 12
Break-Before-Make Time Delay, t <sub>BBM</sub>	70		ns typ	$R_{L} = 300 \Omega, C_{L} = 35 pF$
		10	ns min	$V_{S1} = V_{S2} = 3.3 \text{ V}$ ; see Figure 13
Charge Injection	6		pC typ	$V_{S} = 0 \text{ V}, R_{S} = 0 \Omega, C_{L} = 1 \text{ nF}; \text{ see Figure 14}$
Off Isolation	-67		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 15
Channel-to-Channel Crosstalk	-67		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 16
Bandwidth –3 dB	190		MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ ; see Figure 17
C <sub>s</sub> (OFF)	25		pF typ	f = 1 MHz
$C_D, C_S$ (ON)	95		pF typ	f = 1 MHz
POWER REQUIREMENTS				$V_{DD} = 5.5 \text{ V}$
l <sub>DD</sub>	0.001		μA typ	Digital inputs = 0 V or 5.5 V
		1.0	μA max	

 $<sup>^{\</sup>rm 1}\,\mbox{Guaranteed}$  by design, not subject to production test.

## **ABSOLUTE MAXIMUM RATINGS**

 $T_A = 25$ °C, unless otherwise noted.

Table 3.

Tuble 3.			
Parameter	Rating		
$V_{DD}$ to $V_{SS}$	13 V		
V <sub>DD</sub> to GND	−0.3 V to +6.5 V		
$V_{ss}$ to GND	+0.3 V to −6.5 V		
Analog Inputs <sup>1</sup>	$V_{SS} - 0.3 \text{ V to } V_{DD} + 0.3 \text{ V}$		
Digital Inputs <sup>1</sup>	$-0.3 \text{ V to V}_{DD} + 0.3 \text{ V or } 30 \text{ mA}$		
	(whichever occurs first)		
Peak Current, S or D	100 mA (pulsed at 1 ms,		
	10% duty cycle maximum)		
Continuous Current, S or D	50 mA		
Operating Temperature Range	−55°C to +125°C		
Storage Temperature Range	−65°C to +150°C		
Junction Temperature	150°C		
Thermal impedance			
$\Theta_{JA}$	229.6°C/W		
$\theta_{\sf JC}$	91.99°C/W		
Lead Soldering			
Reflow, Peak Temperature	260(+0/-5)°C		
Time at Peak Temperature	20 sec to 40 sec		

<sup>&</sup>lt;sup>1</sup> Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

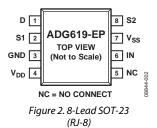
Only one absolute maximum rating may be applied at a time.

## **ESD CAUTION**



**ESD** (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

# PIN CONFIGURATION AND FUNCTION DESCRIPTIONS



**Table 4. Pin Function Descriptions** 

1 word 10 1 m 1 windows 2 dod 17 wow				
Pin No.	Mnemonic	Description		
1	D	Drain Terminal. Can be an input or output.		
2	S1	Source Terminal. Can be an input or output.		
3	GND	Ground (0 V) Reference.		
4	$V_{DD}$	Most Positive Power Supply.		
5	NC	No Connect. Not internally connected.		
6	IN	Logic Control Input.		
7	V <sub>SS</sub>	Most Negative Power Supply. This pin is only used in dual-supply applications and should be tied to ground in single-supply applications.		
8	S2	Source Terminal. Can be an input or output.		

Table 5. Truth Table for the ADG619-EP

IN	Switch S1	Switch S2
0	On	Off
1	Off	On

## TYPICAL PERFORMANCE CHARACTERISTICS

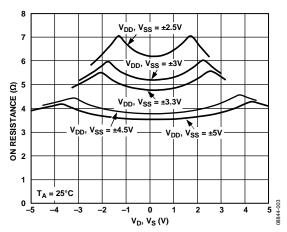


Figure 3. On Resistance vs.  $V_D$ ,  $V_S$  (Dual Supply)

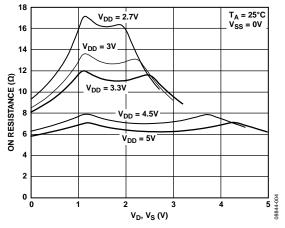


Figure 4. On Resistance vs.  $V_D$ ,  $V_S$  (Single Supply)

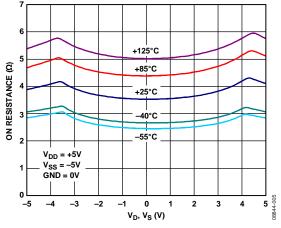


Figure 5. On Resistance vs.  $V_D$ ,  $V_S$  for Different Temperatures (Dual Supply)

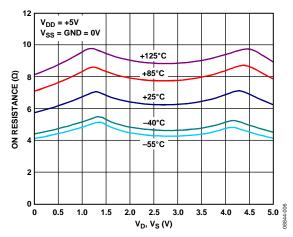


Figure 6. On Resistance vs.  $V_D$ ,  $V_S$  for Different Temperatures (Single Supply)

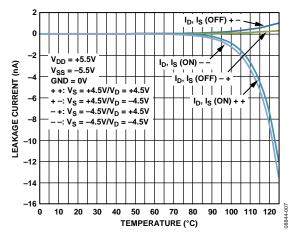


Figure 7. Leakage Currents vs. Temperature (Dual Supply)

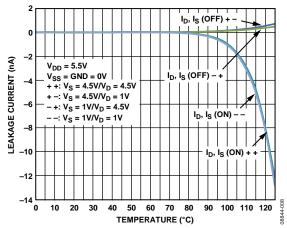


Figure 8. Leakage Currents vs. Temperature (Single Supply)

## **TEST CIRCUITS**

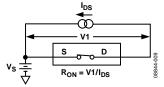


Figure 9. On Resistance

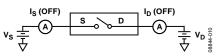


Figure 10. Off Leakage

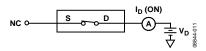
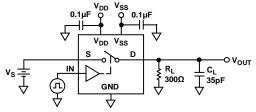


Figure 11. On Leakage



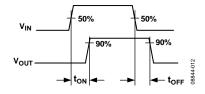
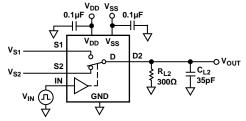


Figure 12. Switching Times



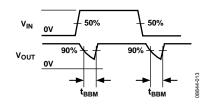


Figure 13. Break-Before-Make Time Delay,  $t_{BBM}$ 

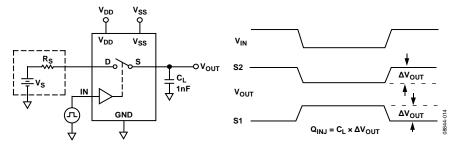


Figure 14. Charge Injection

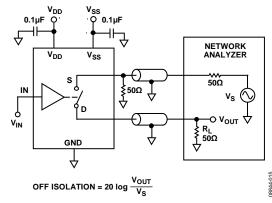


Figure 15. Off Isolation

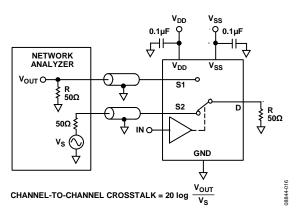


Figure 16. Channel-to-Channel Crosstalk

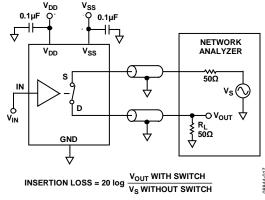


Figure 17. Bandwidth

# **OUTLINE DIMENSIONS**

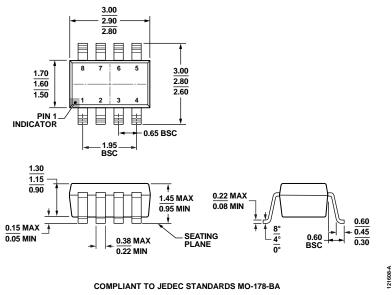


Figure 18. 8-Lead Small Outline Transistor Package [SOT-23] (RJ-8) Dimensions shown in millimeters

## **ORDERING GUIDE**

Model <sup>1</sup>	Temperature Range	Package Description	Package Option	Branding <sup>2</sup>
ADG619SRJZ-EP-RL7	−55°C to +125°C	8-Lead Small Outline Transistor Package [SOT-23]	RJ-8	S3V

<sup>&</sup>lt;sup>1</sup> Z =RoHS Compliant Part.

 $<sup>^{\</sup>rm 2}$  Branding on SOT-23 packages is limited to three characters due to space constraints

# **NOTES**

ADG619-EP
-----------

NOTES